

Φ – 575 Διάλεξη 14

Φυσική διατάξεων δισδιάστατων ημιαγωγών

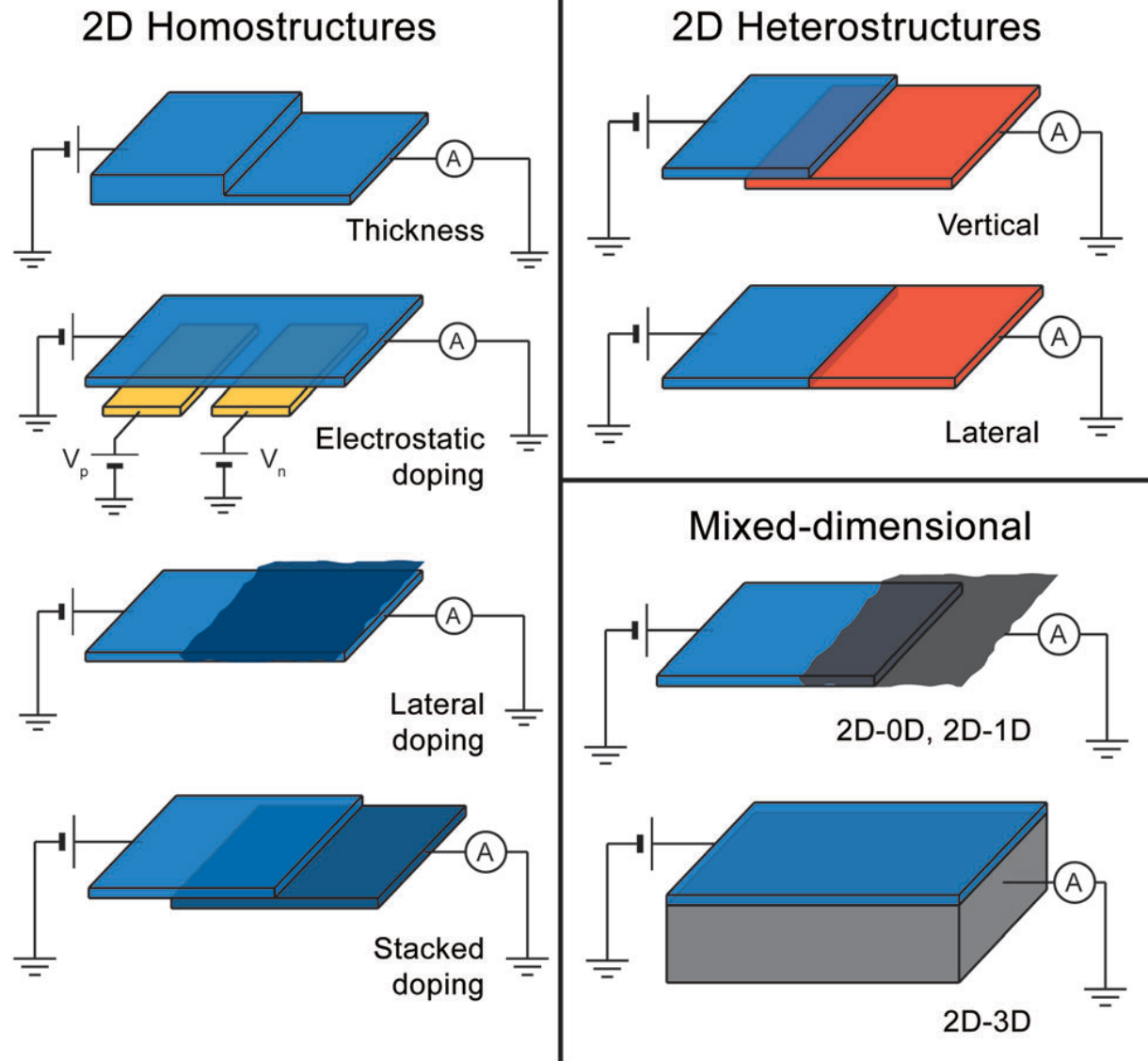
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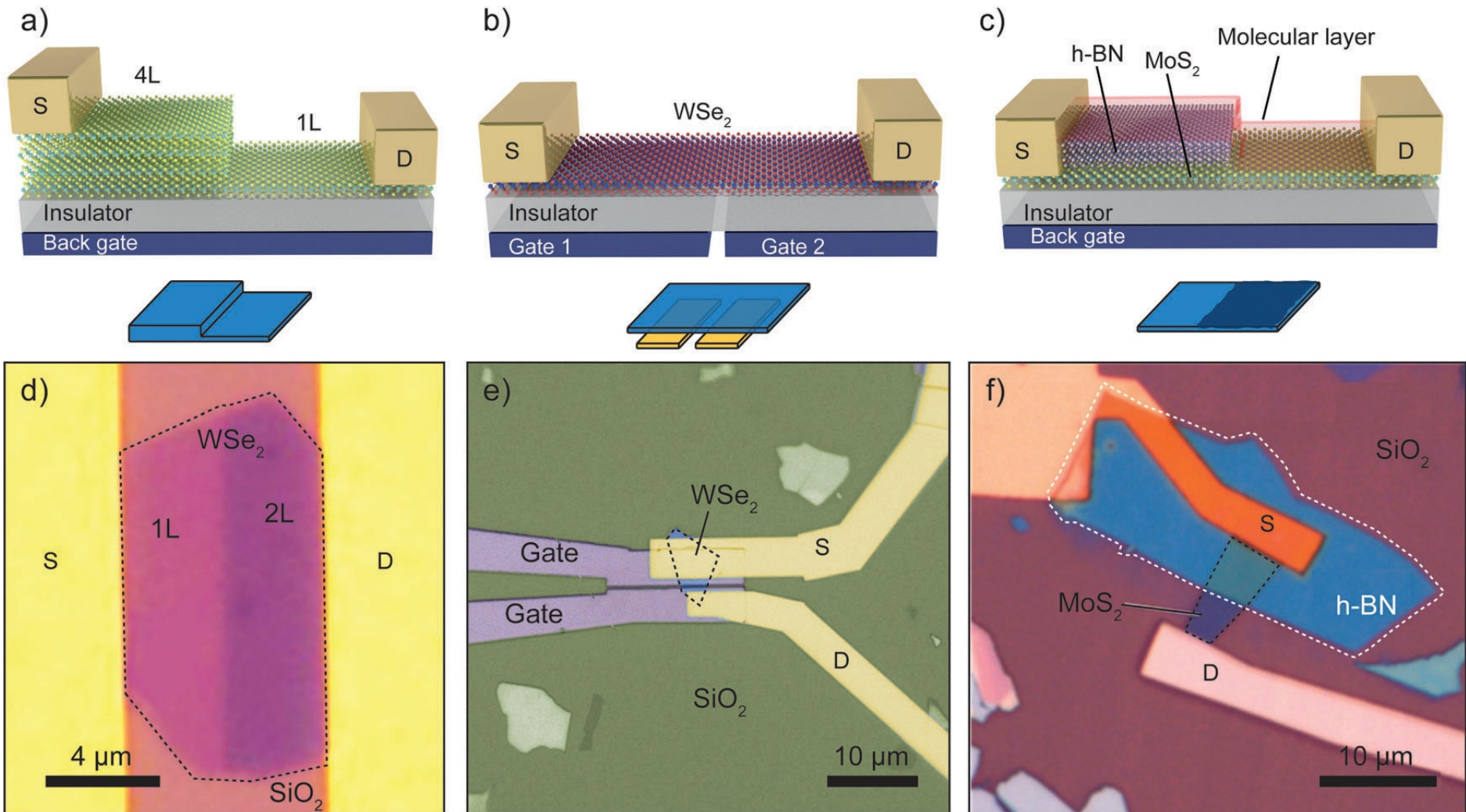
- *Homo – diodes*
 - *P -N doping to form a junction*
 - *Metal contacts?*
- *Hetero – diodes*
 - *Choose different materials*
 - *2D – 2D*
 - *2D – 3D (hybrid junctions)*

Types of 2D junctions



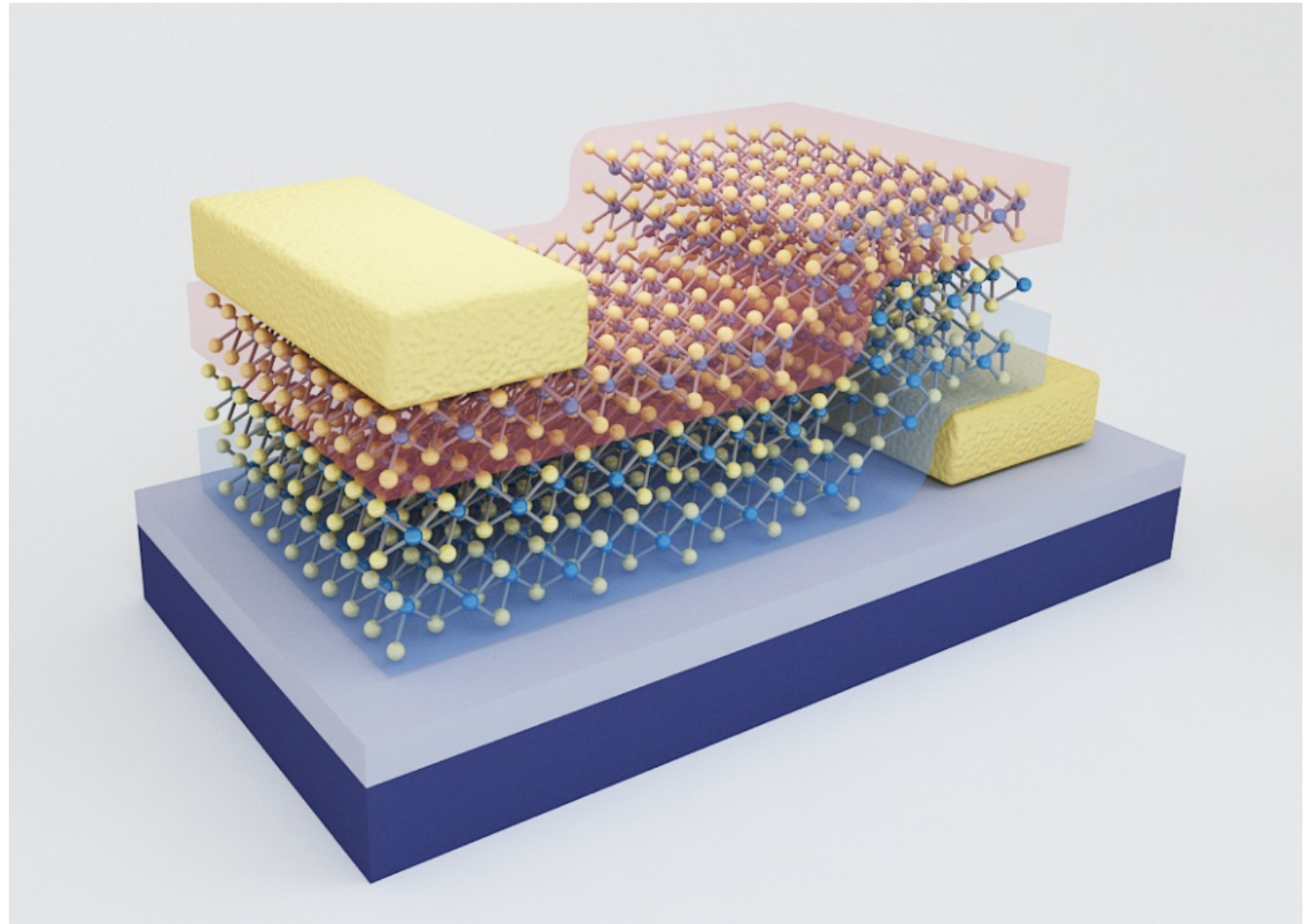
DOI: 10.1039/c7cs00880e

Single layer doping techniques

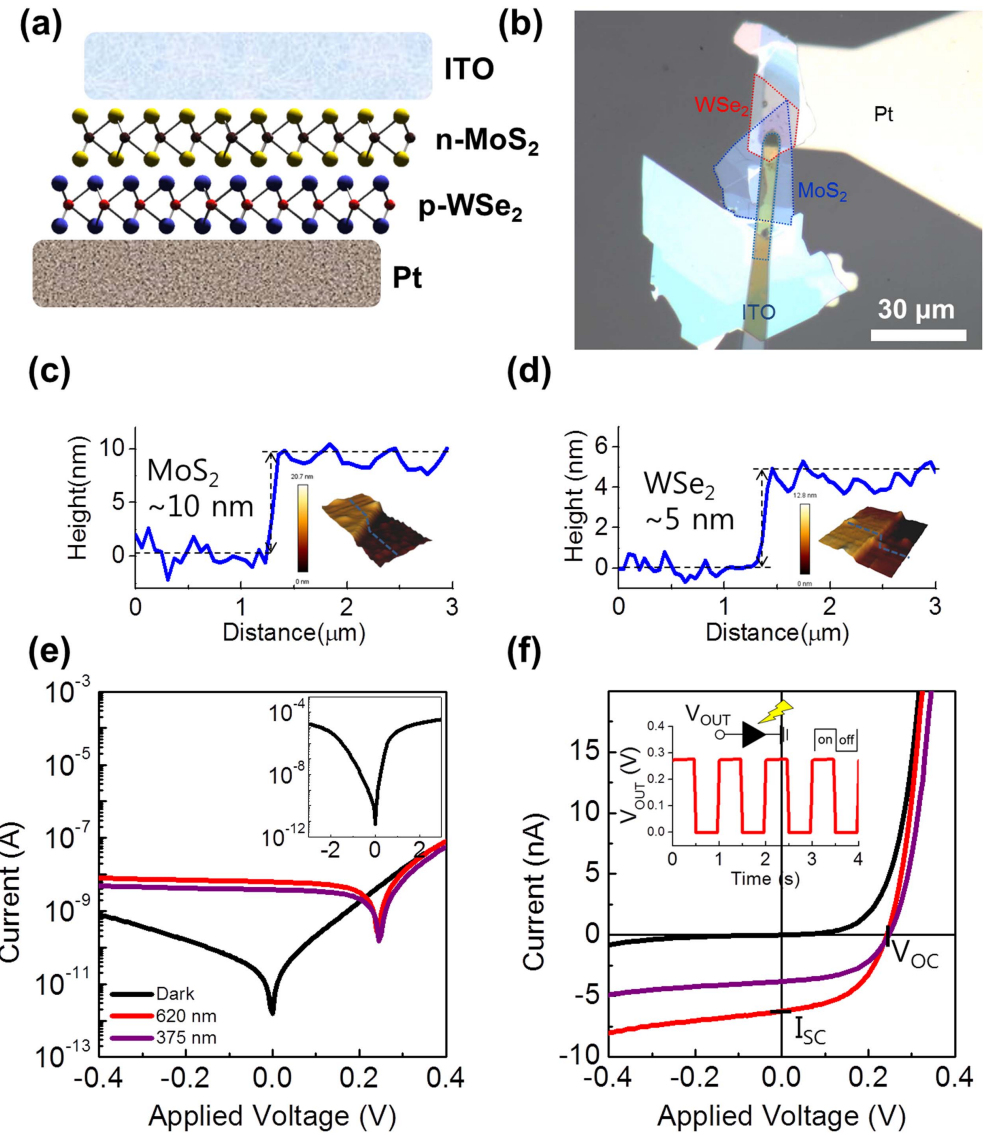


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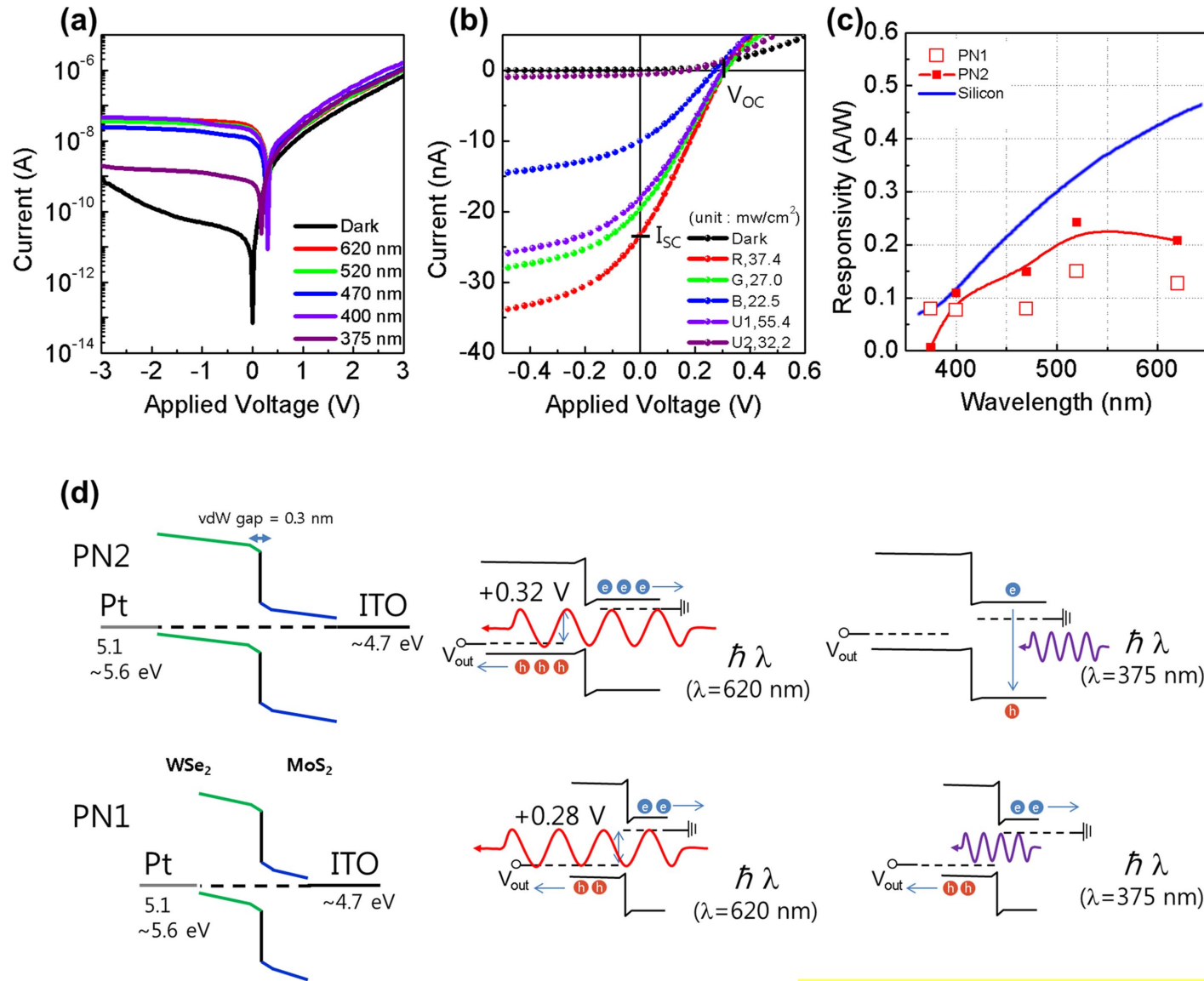
gold chloride (AuCl_3)
and
benzyl viologen (BV).



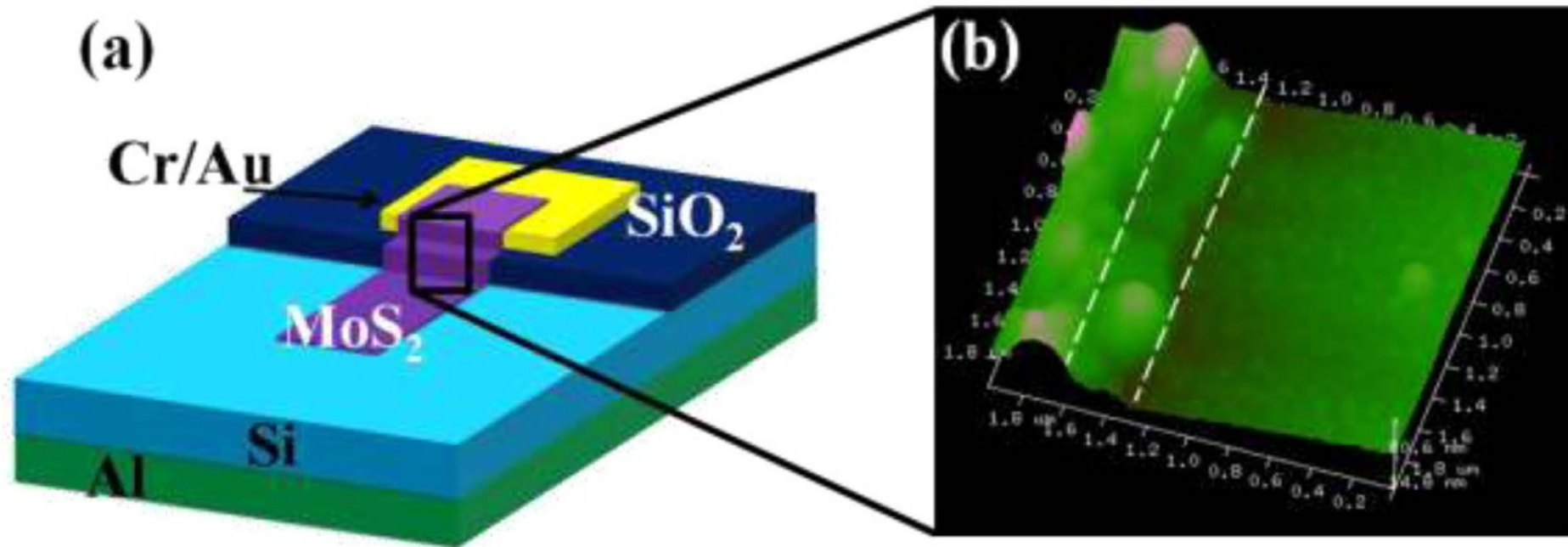
DOI: 10.1038/ncomms7564



doi:10.1088/2053-1583/3/4/045011



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